

BRCS4612SC

Rev.A Aug.-2024



DATA SHEET

SOP-8

MOS

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel

$V_{DS}(V)=60V$

$I_D=9.7A$

$R_{DS(ON)}<16m$ ($V_{GS}=10V$)

$R_{DS(ON)}<22m$ ($V_{GS}=4.5V$)

P-channel

$V_{DS}(V)=-60V$

$I_D=3.4A$

$R_{DS(ON)}<100m$ ($V_{GS}=-10V$)

$R_{DS(ON)}<130m$ ($V_{GS}=-4.5V$)

HF Product.

DC/DC

These devices are well suited for


/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating		Unit	
		N-channel	P-channel		
Drain-Source Voltage	V_{DSS}	60	-60	V	
Gate-Source Voltage	V_{GSS}	±20		V	
Continuous Drain Current	$I_D (T_A=25)$	9.7	-3.4	A	
Pulsed Drain Current	I_{DM}	±40		A	
Power Dissipation	$P_D (T_A=25)$	2.7	1.9	W	
Maximum Junction-to-Ambient	R_{JA}	tm10s	46.3	65.8	/W
		Steady-State	72	100	/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150			

N / N-CHANNEL Electrical Characteristic Curve

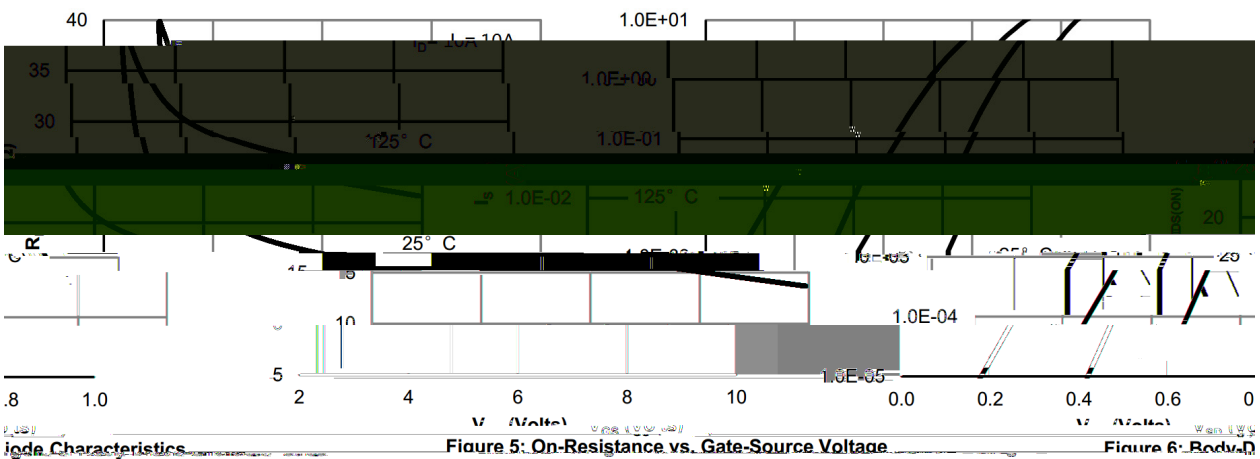
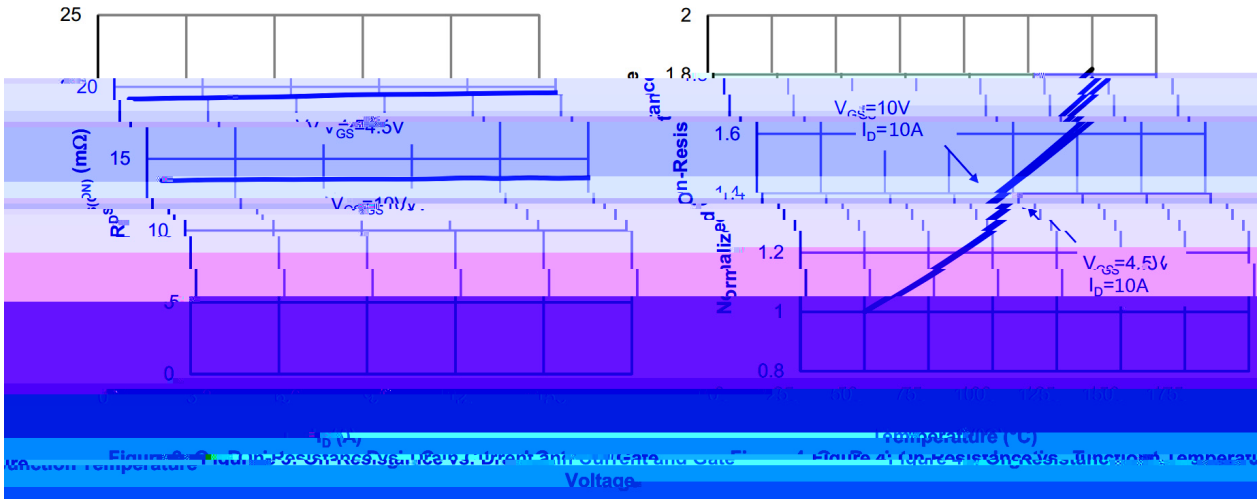
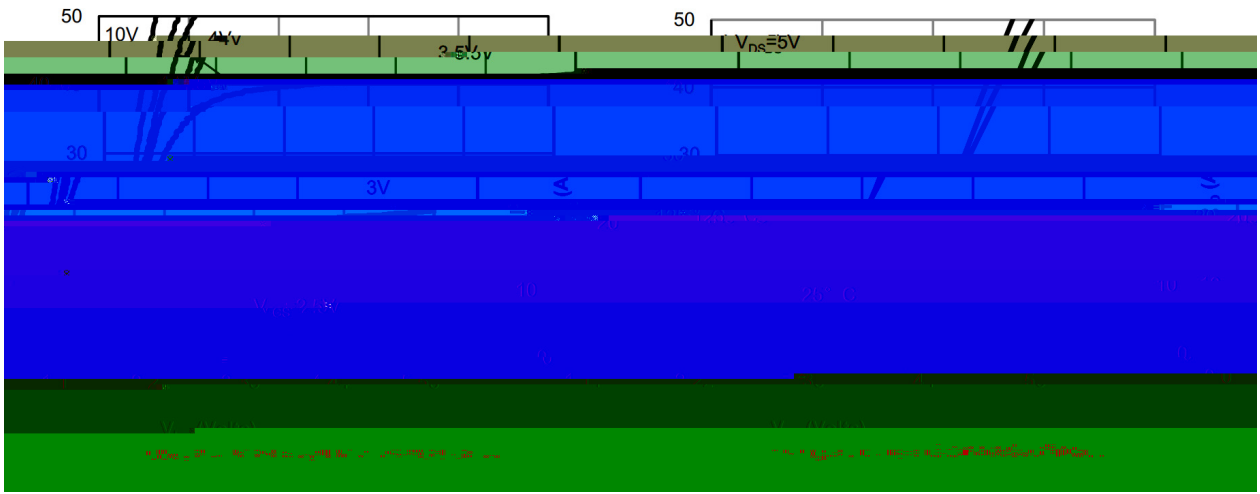
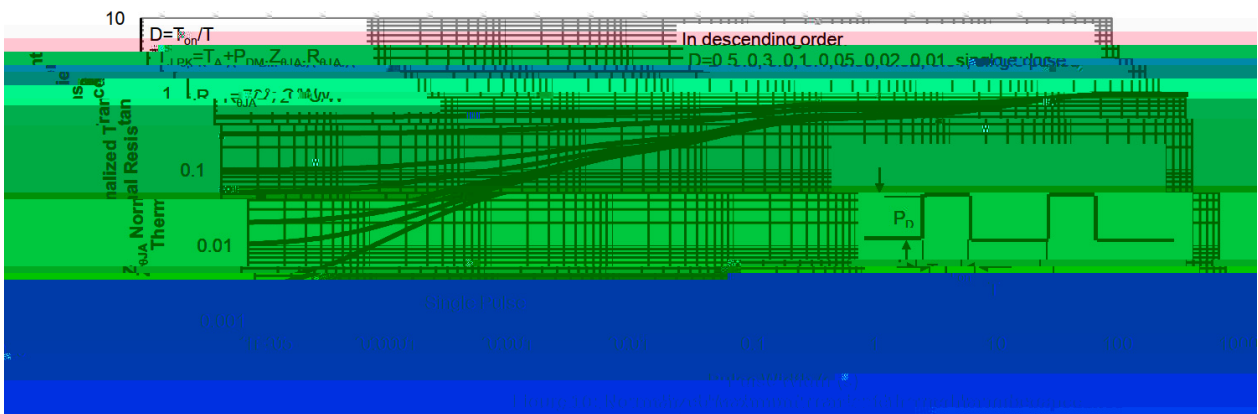
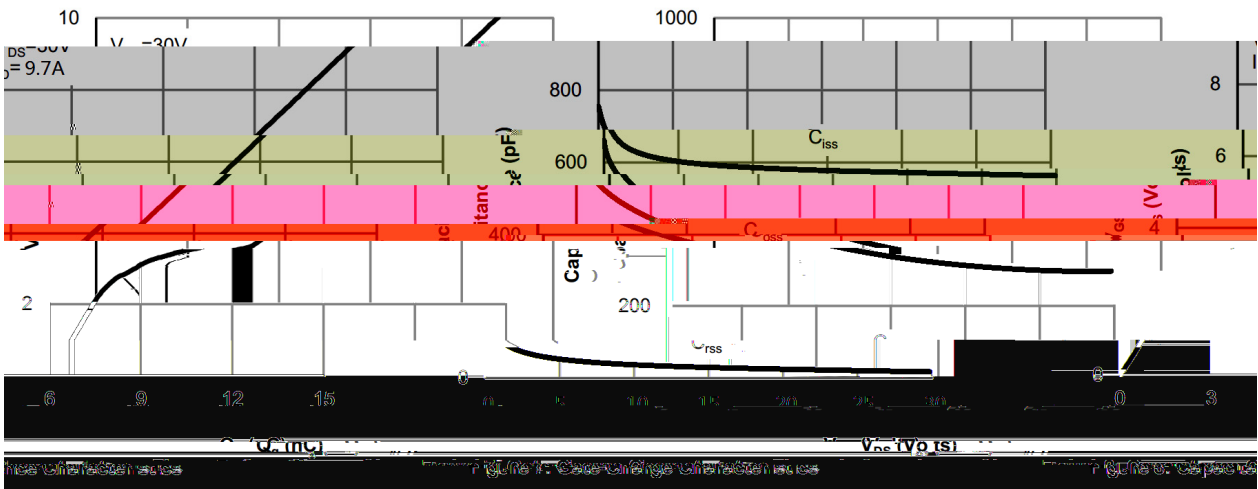


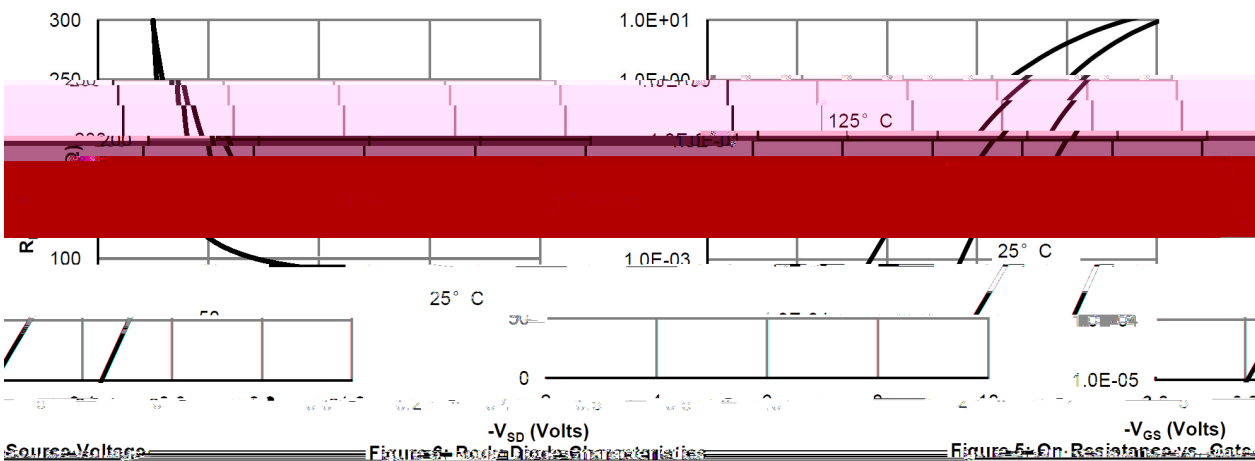
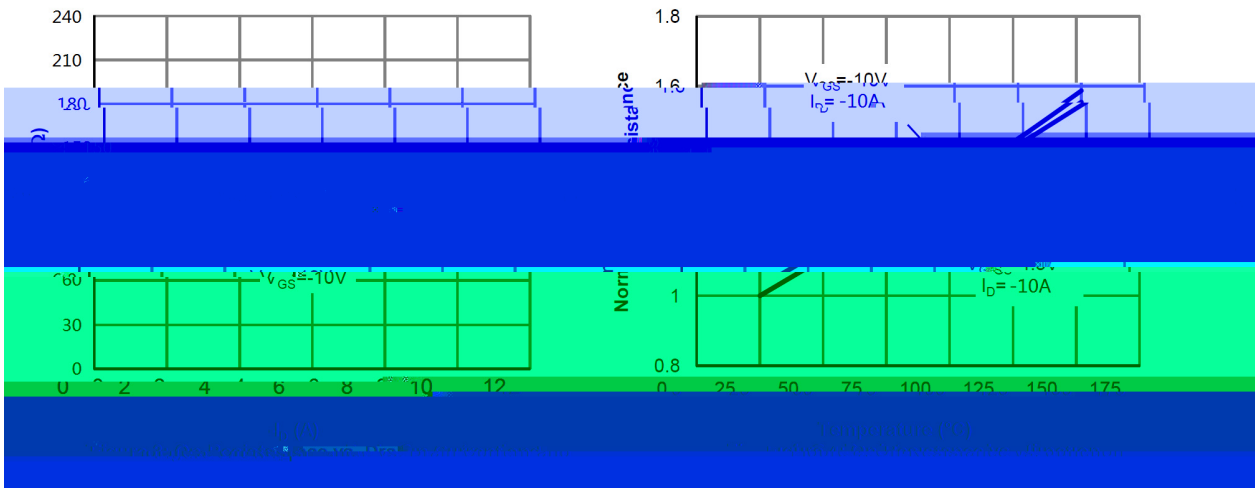
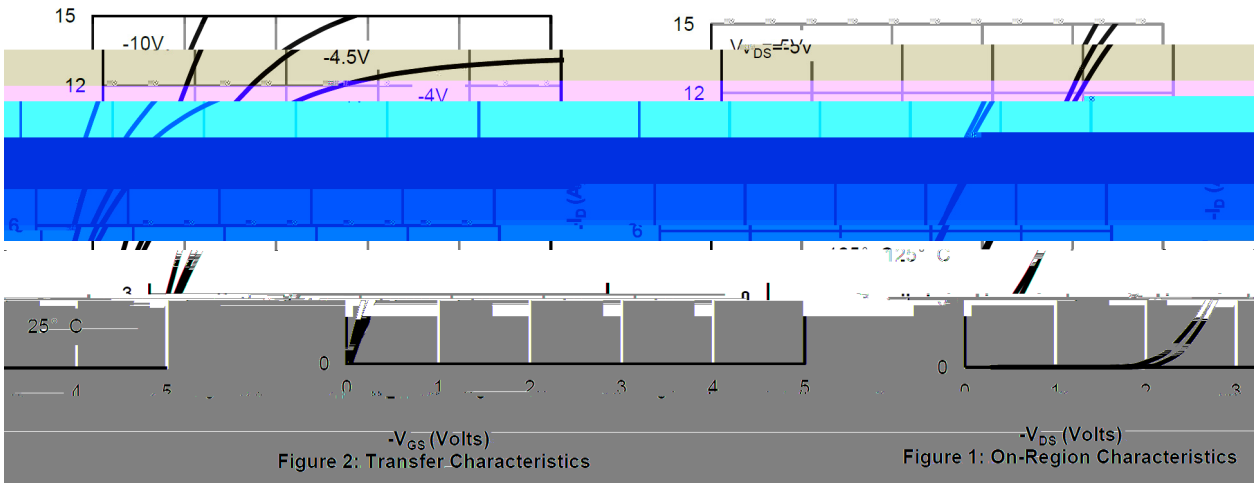
Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: $R_{DS(on)}$

N / N-CHANNEL Electrical Characteristic Curve

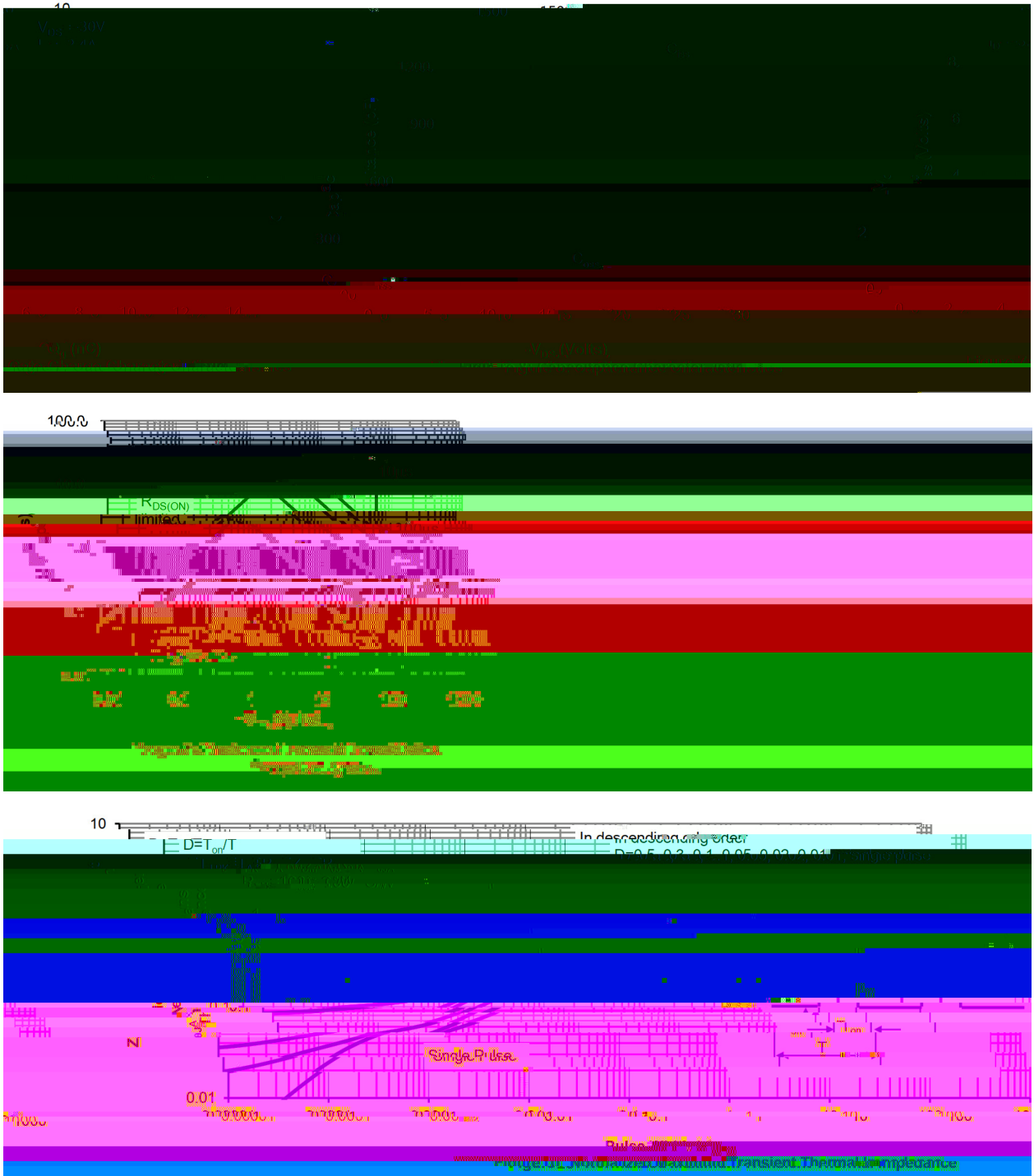


P- / P-CHANNEL Electrical Characteristic Curve



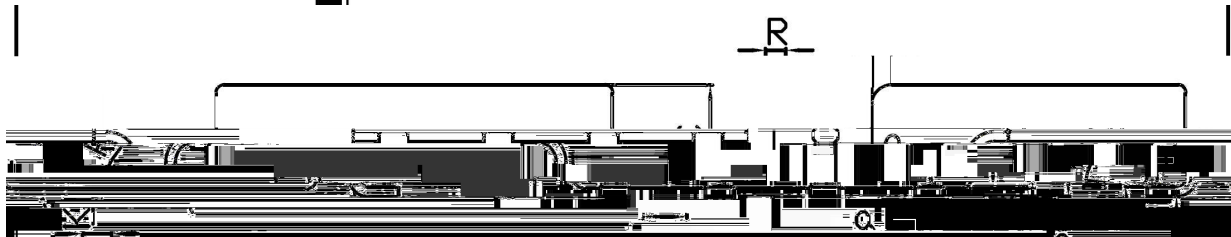
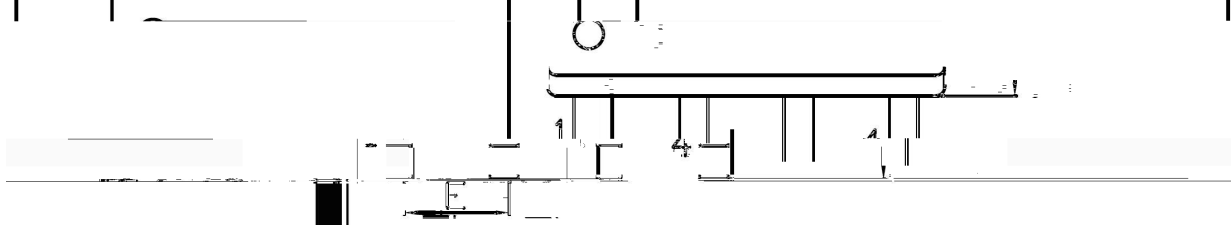
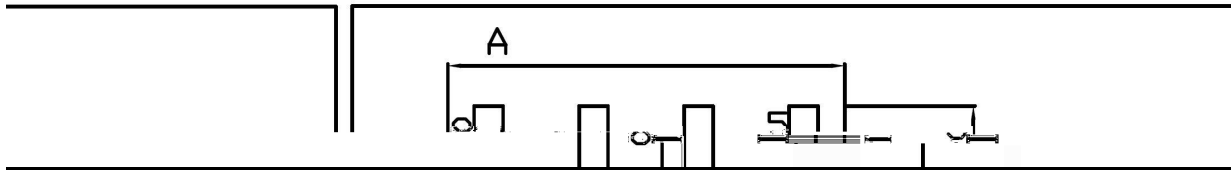
Source Voltage: Figure 6: Body Diode Characteristics Figure 7: On-Resistance vs. Gate

P- / P-CHANNEL Electrical Characteristic Curve



/ Package Dimensions

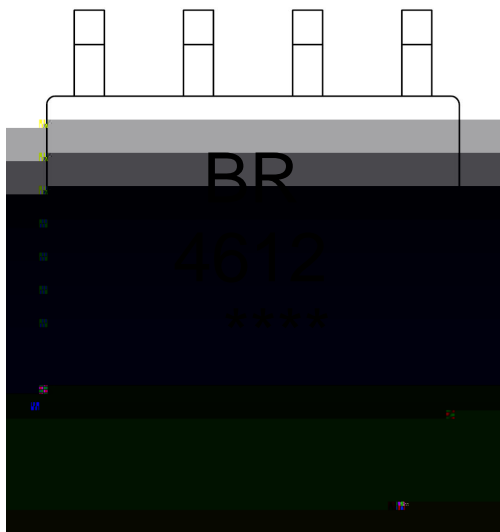
02P 0 1.0mm 5.0mm 8.0mm



Symbol	Dimensions in Millimeters	Symbol	Dimensions in Millimeters
A	4.70	J	5.10
B	7.00	K	4.00
C	8.00	L	1.70
D	1.40	M	0.20
E	0.20	N	0.20
F	0.20	O	0.20
G	0.20	P	0.20
H	0.20	Q	0.20
I	0.20	R	0.20



/ Marking Instructions



BR

4612

Note:

BR: Company Code

4612: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

1 150 180 60 90sec; Note: 1.Preheating: 10.5 127.3(1.Pr.Preheatin.)-1260 668.TD0